The 1N66 is a hermetically sealed point contact germanium diode designed for use in general purpose rectifier applications and gate leg or buffer circuits in computers. The 1N66 is particularly applicable where medium back resistance, small size, absence of heater voltage, low shunt capacitance and resistance to changes in humidity and temperature are important. Operable at temperatures up to 100°C, it can be heated as high as 125°C with no irreversible change in characteristics. Each diode is dynamically tested for hysteresis, drift, and flutter. The 1N66 has extremely uniform electrical characteristics and reliable mechanical stability.

MECHANICAL DATA

TERMINALS: Dumet wire, Tinned to within 1/8" of barrel
Diameter: .017" max. Length: 1" min.

TERMINAL CONNECTIONS: White Band at Cathode Terminal

MOUNTING POSITION: Any

PLUG-IN EQUIVALENT: Available as 1N66-P

ELECTRICAL DATA

RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)

- Inverse Voltage
  - Average Rectified Current
  - Peak Rectified Current
  - Surge Current (for 1 sec.)
- Ambient Temperature Range
- Dissipation at:
  - 25°C
  - 50°C
  - 75°C
  - 100°C

CHARACTERISTICS: (at 25°C)

- Maximum Inverse Current at -10 volts
- Maximum Inverse Current at -50 volts
- Minimum Forward Current at +1 volt
- Shunt Capacitance
- Minimum Reverse Voltage for Zero Dynamic Resistance

* Each diode receives repeated humidity cycling, and additional temperature cycling ranging from -25°C to 130°C.

TYPICAL STATIC CHARACTERISTICS (at 25°C)

Tentative Data